



## SUBSTITUTE SPECIFICATION

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TITLE OF THE INVENTION  
SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

BACKGROUND OF THE INVENTION

5 Field of the Invention

The present invention relates to a semiconductor integrated circuit device having a decoupling capacitor, and, more particularly, to a semiconductor integrated circuit device with an improved device integration density.

10 Description of the Related Art

As operational frequencies of semiconductor integrated circuit devices have become increasingly higher, there is a tendency for the wiring area allocated to the power supply wire and ground wire to also become larger. Thus, when a semiconductor integrated circuit device operates at high frequency, a variation in power supply voltage, such as temporary current spike, is likely to occur.

As a conventional scheme to suppress this variation in power supply voltage, there is known a technique of connecting a decoupling capacitor in parallel to the power supply. This connection can reduce power supply noise and suppress a variation in power supply voltage, which leads to 1) prevention of the malfunction of a semiconductor integrated circuit originated from power supply noise and, 2) a variation in power supply voltage. To achieve the above object, the size of the decoupling capacitor connected

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to the power supply should be set to several tens of nF with respect to a single chip or package. In the conventional semiconductor integrated circuit device, an exclusive layout area for a decoupling capacitor is provided at each side of space between the core portion or the device forming region and the I/O portion, and the decoupling capacitor is formed by MOS (Metal Oxide Semiconductor).

However, in a conventional semiconductor integrated circuit device the need for the exclusive layout area for a decoupling capacitor increases the device area and lowers the device integration density.

An example of a solution to this problem, Japanese Patent Laid-Open No. 12825/1998, discloses a technique of forming a polycrystalline silicon layer on the device side of a semiconductor substrate and forming a decoupling capacitor between the polycrystalline silicon layer and the top surface of the semiconductor substrate. The technique this patent describes eliminates the need for the exclusive layout area for a decoupling capacitor.

Due to the decoupling capacitor formation on the device side of a device forming region according to the conventional technique, a problem arises in that the area of the device forming region increases.

Japanese Patent Laid-Open No. 2002-124636 discloses a technique of providing a multilayer wiring structure on a semiconductor element and forming 1) an electrode, 2) a

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dielectric film and 3) an electrode on the multilayer wiring structure in the named order; thereby forming a decoupling capacitor. Japanese Patent Laid-Open No. 2002-124636 describes that this technique allows a large-capacitance  
5 decoupling capacitor to be provided in a semiconductor device.

However, the above conventional technique has a problem. Because a decoupling capacitor is provided on the multilayer wiring structure according to the technique described in  
10 Japanese Patent Laid-Open No. 2002-124636, pad electrodes cannot be provided in the region on the multilayer wiring structure where the decoupling capacitor is provided. This restricts the layout of the semiconductor integrated circuit device and enlarges it as a consequence. Also, providing a  
15 decoupling capacitor on the multilayer wiring structure requires at least the step of forming a lower electrode layer, the step of forming a dielectric layer and the step of forming an upper electrode layer, which complicates the fabrication process for the semiconductor integrated circuit  
20 device and increases the fabrication cost.

#### SUMMARY OF THE INVENTION

Accordingly, it is an object of the invention to provide a semiconductor integrated circuit device having a  
25 decoupling capacitor, which does not require an exclusive layout area for the decoupling capacitor and is easy to

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fabricate.

A semiconductor integrated circuit device, according to the invention, comprises: 1) a first conductivity type semiconductor substrate connected to a first power supply;  
5 2) a second conductivity type semiconductor layer provided on the first conductivity type semiconductor substrate or at a top surface of the first conductivity type semiconductor substrate and connected to a second power supply; and 3) a device forming portion provided on the second conductivity  
10 type semiconductor layer; with a decoupling capacitor formed at an interface between the first conductivity type semiconductor substrate and the second conductivity type semiconductor layer.

According to the invention, as the decoupling capacitor  
15 connected in parallel to the power supply is formed at the interface between the first conductivity type semiconductor substrate and the second conductivity type semiconductor layer, the power supply noise and a variation in power supply voltage can be suppressed, thus preventing the  
20 malfunction of the semiconductor integrated circuit device. The provision of the decoupling capacitor connected in parallel to the power supply at the interface between the first conductivity type semiconductor substrate and the second conductivity type semiconductor layer eliminates an  
25 exclusive layout area for the decoupling capacitor and effectively makes the device smaller. Further, the

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decoupling capacitor can be formed easily by forming the second conductivity type semiconductor layer, so that both the fabrication process does not become complicated and the actual fabrication becomes easier.

5           The second conductivity type semiconductor layer may be provided on an entire top surface of the first conductivity type semiconductor substrate or on the entire top surface of the first conductivity type semiconductor substrate, and a bottom surface of the first conductivity type semiconductor  
10       substrate may be connected to the first power supply. This makes it possible to form a decoupling capacitor on the first conductivity type semiconductor substrate or the entire top surface of the first conductivity type semiconductor substrate, yielding a large-capacitance  
15       decoupling capacitor.

          At this time, the device forming portion may have a first conductivity type well contacting the second conductivity type semiconductor layer and connected to a third power supply and another decoupling capacitor may be  
20       formed at an interface between the first conductivity type well and the second conductivity type semiconductor layer.

          The device forming portion may have another second conductivity type semiconductor layer electrically connected to the second conductivity type semiconductor layer, and a  
25       first conductivity type well provided on the another second conductivity type semiconductor layer contacted with the

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another second conductivity type semiconductor layer and  
connected to a third power supply, and another decoupling  
capacitor may be formed at an interface between the first  
conductivity type well and the another second conductivity  
5 type semiconductor layer.

This makes it possible to form another decoupling  
capacitor connected in parallel to the first decoupling  
capacitor. As a result, the total capacitance of the  
decoupling capacitors can be increased. The device forming  
10 portion may have an active element connected to the third  
power supply, or the potential of the third power supply may  
differ from potentials of the first and second power  
supplies. This makes it possible to independently set the  
voltage for driving the active element and the voltage for  
15 forming the decoupling capacitor and optimally adjusting the  
voltages.

The second conductivity type semiconductor layer may be  
locally provided on the first conductivity type  
semiconductor substrate or at the top surface of the first  
20 conductivity type semiconductor substrate. The device  
forming portion may be formed in the region in the top  
surface of the first conductivity type semiconductor  
substrate where the second conductivity type semiconductor  
layer is not provided. The first conductivity type  
25 semiconductor substrate may be connected to the first power  
supply via the device forming portion. This makes it

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possible to control the capacitance by adjusting the area of the decoupling capacitor and also makes it unnecessary to connect the bottom side of the first conductivity type semiconductor layer to the first power supply. The mounting  
5 therefore becomes easier.

The first conductivity type semiconductor substrate may have a substrate body, and a surface portion having a lower resistivity than that of the substrate body. Accordingly, the decoupling capacitor can be formed between the top layer  
10 portion of the first conductivity type semiconductor substrate whose resistivity is lower than that of the substrate body and the second conductivity type semiconductor layer, which increases the capacitance of the decoupling capacitor.

15 Another semiconductor integrated circuit device, according to the invention comprises 1) a first conductivity type semiconductor substrate connected to a first power supply; and 2) a device forming portion provided on the first conductivity type semiconductor substrate and having a  
20 second conductivity type well connected to a second power supply, with a decoupling capacitor formed at an interface between the first conductivity type semiconductor substrate and the second conductivity type well.

According to the invention, the decoupling capacitor  
25 connected to the power supply is formed at the interface between the first conductivity type semiconductor substrate



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and the second conductivity type well formed in the device forming portion. Accordingly, power supply noise and a variation in power supply voltage can be suppressed, thus preventing the malfunction of the semiconductor integrated  
5 circuit device. This also eliminates the need for an exclusive layout area for the decoupling capacitor which can make the device smaller. Further, the decoupling capacitor can be formed easily by forming the second conductivity type well so that both the fabrication process does not become  
10 complicated and the actual fabrication becomes easier.

A further semiconductor integrated circuit device according to the invention comprises a substrate; a first first conductivity type semiconductor layer connected to a first power supply provided at least a part of the  
15 substrate; a second conductivity type semiconductor layer provided on the first first conductivity type semiconductor layer and connected to a second power supply; and a device forming portion provided on the second conductivity type semiconductor layer, with a decoupling capacitor formed at  
20 an interface between the first first conductivity type semiconductor layer and the second conductivity type semiconductor layer.

According to the invention, a decoupling capacitor connected to the power supply is formed at the interface  
25 between the first conductivity type semiconductor substrate and the second conductivity type semiconductor layer.

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Accordingly, power supply noise and a variation in power supply voltage can be suppressed, thus preventing the malfunction of the semiconductor integrated circuit device and eliminating the need for an exclusive layout area for the decoupling capacitor, which can make the device smaller. Further, as the decoupling capacitor can be formed easily by forming the second conductivity type semiconductor layer, the fabrication process does not become complicated and the actual fabrication becomes easier.

10           The first first conductivity type semiconductor layer may be provided selectively on the substrate, the device may also have a second first conductivity type semiconductor layer (provided in that region where the first conductivity type semiconductor layer and the second conductivity type semiconductor layer are not provided) connected to the first conductivity type semiconductor layer and the first power supply, and the first conductivity type semiconductor layer may be connected to the first power supply via the device forming portion and second first conductivity type semiconductor layer. This allows the first conductivity type semiconductor layer to be connected to the first power supply by a simple structure.

25           It is preferable that the substrate have a resistivity of 100  $\Omega$ ·cm or higher. This can suppress transmission of noise in the substrate and can reliably prevent the malfunction of the semiconductor integrated circuit device.

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Furthermore, it is preferable that the device forming portion should have an active element connected to third and fourth power supplies, and the potential of the third power supply should differ from potentials of the first and second power supplies. This makes it possible to independently set the voltage for driving the active element, forming the decoupling capacitor, and optimally adjusting the voltages.

According to the invention, because the decoupling capacitor connected in parallel to the power supply is formed at the interface between the first conductivity type semiconductor substrate and the second conductivity type semiconductor layer, power supply noise and a variation in power supply voltage can be suppressed. This can prevent the malfunction of the semiconductor integrated circuit device. It also eliminates an exclusive layout area for the decoupling capacitor, so the device can be made smaller. Since the capacitor can be formed easily by forming the second conductivity type semiconductor layer, it is possible to form the capacitor easily.

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#### BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a cross-sectional view showing a semiconductor integrated circuit device according to a first embodiment of the invention;

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Fig. 2 is a cross-sectional view showing a semiconductor integrated circuit device according to a

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second embodiment of the invention;

Fig. 3 is a cross-sectional view showing a semiconductor integrated circuit device according to a third embodiment of the invention;

5 Figs. 4A and 4B are graphs showing the concentration distribution of the semiconductor integrated circuit device with the depth-directional position in the semiconductor integrated circuit device taken on the horizontal axis and the impurity concentration taken on the vertical axis. Fig.  
10 4A shows the concentration distribution of the semiconductor integrated circuit device according to the third embodiment. Fig. 4B shows the concentration distribution of the semiconductor integrated circuit device according to the first embodiment;

15 Fig. 5 is a cross-sectional view showing a semiconductor integrated circuit device according to a fourth embodiment of the invention;

Fig. 6 is a cross-sectional view showing a semiconductor integrated circuit device according to a fifth  
20 embodiment of the invention; and

Fig. 7 is a cross-sectional view showing a semiconductor integrated circuit device according to a sixth embodiment of the invention.

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#### DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Preferred embodiments of the invention will be described specifically below with reference to the accompanying drawings. Fig. 1 is a cross-sectional view showing a semiconductor integrated circuit device 1a according to the first embodiment. As shown in Fig. 1, an N type silicon substrate, Nsub, is provided in the semiconductor integrated circuit device 1a. The N type silicon substrate, Nsub, has a resistivity of, for example, 10  $\Omega\cdot\text{cm}$  and is connected to a power supply terminal (not shown) from its bottom side (not shown). A P type epitaxial layer PEpi2 is formed on the entire surface of the N type silicon substrate Nsub. The P type epitaxial layer PEpi2 has a resistivity of, for example, 0.3  $\Omega\cdot\text{cm}$ . The N type silicon substrate Nsub has a thickness of, for example, 0.3 to 0.6  $\mu\text{m}$ . The P type epitaxial layer PEpi2 has a thickness of, for example, 1 to 5  $\mu\text{m}$ . As a power supply potential and a ground potential are respectively applied to the N type silicon substrate Nsub and P type epitaxial layer PEpi2, a pn junction is formed at the interface between them and a capacitor C1 is formed at that interface. In other words, the capacitor C1 shown in Fig. 1 equivalently shows a decoupling capacitor which is formed by the pn junction at the interface between the N type silicon substrate Nsub and the P type epitaxial layer PEpi2.

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A device forming portion 2 is then provided on the P type epitaxial layer PEpi2. In the device forming portion 2, a P type epitaxial layer PEpi1 and an interlayer insulating film 3 are provided and an N well NW and P well PW are  
5 formed on the top surface of the P type epitaxial layer PEpi1. The P type epitaxial layer PEpi1 has a resistivity of, for example,  $10 \Omega \cdot \text{cm}$  and has a thickness of, for example, 1 to 5  $\mu\text{m}$ . The interlayer insulating film 3 is located on the N well NW and P well PW. As the ground potential and  
10 the power supply potential are respectively applied to the P type epitaxial layer PEpi1 and the N well NW, a pn junction is formed at the interface between them and a capacitor C6 is formed at that interface. That is, the capacitor C6 shown in Fig. 1 equivalently shows a decoupling capacitor  
15 which is formed by the pn junction at the interface between the P type epitaxial layer PEpi1 and the N well NW. At this time, the capacitors C1 and C6 are connected in parallel to each other.

The top surfaces of the N well NW and the P well PW are  
20 separated by device isolation films S and an  $n^+$  diffusion region ND1, p channel transistors PTr1 and PTr2 and a capacitor C11 are provided between the device isolation films S on the top surface of the N well NW. Provided on the  $n^+$  diffusion region ND1 is a via V1 on which a wire W1  
25 is provided. The  $n^+$  diffusion region ND1 is connected to the wire W1 via the via V1. The  $n^+$  diffusion region ND1 is

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connected to a power supply terminal (not shown) via the via  
V1 and the wire W1. The power supply terminal to which the  
n<sup>+</sup> diffusion region ND1 is connected is different from the  
power supply terminal to which the N type silicon substrate  
5 Nsub is connected.

In the p channel transistor PTr1, p<sup>+</sup> diffusion regions  
PD1 and PD2, which become a source and drain, are formed in  
the top surface of the N well NW and the area between the p<sup>+</sup>  
diffusion regions PD1 and PD2 on the N well NW is a channel  
10 region. A gate electrode G1 is provided above the channel  
region in the interlayer insulating film 3. That is, a part  
of the interlayer insulating film 3 is intervened between  
the N well NW and the gate electrode G1 and serves as a gate  
insulating film. Vias V2 and V3 are respectively provided  
15 on the p<sup>+</sup> diffusion region PD1 and p<sup>+</sup> diffusion region PD2  
and wires W2 and W3 are respectively provided on the vias 2  
and 3. The p<sup>+</sup> diffusion region PD1 is connected to the wire  
W2 via the via V2 and the p<sup>+</sup> diffusion region PD2 is  
connected to the wire W3 via the via V3. That is, the p  
20 channel transistor PTr1 comprises the N well NW, the p<sup>+</sup>  
diffusion regions PD1 and PD2, the gate electrode G1 and the  
interlayer insulating film 3.

Likewise, the p channel transistor PTr2 comprises the N  
well NW, p<sup>+</sup> diffusion regions PD3 and PD4, a gate electrode  
25 G2 and the interlayer insulating film 3, and the p<sup>+</sup>  
diffusion regions PD3 and PD4, which become a source and

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drain, and are respectively connected to wires W4 and W5 via  
respective vias V4 and V5. In the capacitor C11, an  
electrode layer 4 is provided in the interlayer insulating  
film 3 and a part of the interlayer insulating film 3 is  
5 intervened between the N well NW and the electrode layer 4.  
Provided on the electrode layer 4 is a via V6 on which a  
wire W6 is provided. The electrode layer 4 is connected to  
the wire W6 via the via V6.

Provided between the device isolation films S on the  
10 top surface of the P well PW are n channel transistors NTr1  
and NTr2, and a p<sup>+</sup> diffusion region PD5. Like the p channel  
transistors PTr1 and PTr2, the n channel transistor NTr1  
comprises the P well PW, n<sup>+</sup> diffusion regions ND2 and ND3  
which become a source and drain, a gate electrode G3 and the  
15 interlayer insulating film 3, and the n<sup>+</sup> diffusion regions  
ND2 and ND3 are respectively connected to wires W7 and W8  
via respective vias V7 and V8. The n channel transistor  
NTr2 comprises 1) the P well PW, 2) n<sup>+</sup> diffusion regions ND4,  
and ND5 (which become a source and drain), 3) a gate  
20 electrode G4 and 4) the interlayer insulating film 3, and  
the n<sup>+</sup> diffusion regions ND4 and ND5 are respectively  
connected to wires W9 and W10 via respective vias V9 and V10.  
Provided on the p<sup>+</sup> diffusion region PD5 is a via V11 on  
which a wire W11 is provided. The p<sup>+</sup> diffusion region PD5  
25 is connected to a ground terminal (not shown) via the via  
V11 and the wire W11. In the device forming portion 2, the



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gate electrodes G1 to G4 and the electrode layer 4 are provided in the same layer, and the wires W1 to W11 are provided in the same layer.

5 In the semiconductor integrated circuit device 1a, the P type epitaxial layer PEpi2 is connected to the ground terminal via the P type epitaxial layer PEpi1, the P well PW, the p<sup>+</sup> diffusion region PD5, the via V11 and the wire W11. The N type silicon substrate Nsub is connected to the power supply terminal. A pn junction is formed at the interface  
10 between the N type silicon substrate Nsub and the P type epitaxial layer PEpi2, thereby forming the capacitor C1 there. Likewise, a pn junction is formed at the interface between the P type epitaxial layer PEpi1 and the N well NW, thereby forming the capacitor C6.

15 According to the embodiment, the capacitor C1 can be between the N type silicon substrate Nsub and the P type epitaxial layer PEpi2. Further, the capacitor C6 can be formed between the P type epitaxial layer PEpi1 and the N well NW. The capacitors C1 and C6 function as a decoupling  
20 capacitor with respect to the power supply. Therefore, in the semiconductor integrated circuit device 1a, a large capacitor can be formed without providing an exclusive layout area for the decoupling capacitor, and power supply noise can thus be suppressed. This can prevent the  
25 malfunction of the device originated from power supply noise and can make the semiconductor integrated circuit device 1a

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smaller.

Because a decoupling capacitor is not provided above the device forming portion 2 in the embodiment, the layout of the device forming portion 2 is not restricted. This can  
5 contribute to making the semiconductor integrated circuit device 1a smaller.

Further, the power supply terminal to which the  $n^+$  diffusion region ND1 is connected and the power supply terminal to which the N type silicon substrate Nsub is  
10 connected are respectively connected to different power supplies in the embodiment. It is possible to make the potential to be applied to the  $n^+$  diffusion region ND1 different from the potential to be applied to the N type silicon substrate Nsub. The voltage applied to the  $n^+$   
15 diffusion region ND1 drives the p channel transistors PTr1 and PTr2 is set to 1 V. When the voltage is applied to the N type silicon substrate Nsub so that a capacitor is formed between this potential and the ground potential is set to 2 V (for instance), the p channel transistors PTr1 and PTr2  
20 can be driven fast and the capacitance of the capacitor C1 can be increased. Both power supply terminals may be connected together into the same power supply (not shown) outside the semiconductor integrated circuit device 1a, which simplifies the circuit structure.

25 Although an example where the P type epitaxial layer PEpi2 is formed as the second conductivity type

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semiconductor layer on the N type silicon substrate Nsub as the first conductivity type semiconductor substrate has been illustrated in the foregoing description of the first embodiment, the invention is not limited to this particular structure. For example, after the formation of the device forming portion 2 on the N type silicon substrate Nsub, an impurity can be ion-injected into the surface layer of the N type silicon substrate Nsub with energy high enough to penetrate the device forming portion 2, so that a P type layer having the same impurity concentration as the P type epitaxial layer PEpi2 can be formed. This can create the P type layer which is equivalent to the P type epitaxial layer PEpi2 through a simple process without influencing the device forming portion 2.

Although an example where the N type silicon substrate Nsub is used as the substrate has been illustrated in the foregoing description of the first embodiment, a P type silicon substrate may also be used as the substrate. In this case, an N type epitaxial layer or an N type layer formed by ion injection is formed on the P type silicon substrate, thereby forming a capacitor between the P type silicon substrate and the N type epitaxial layer. Further, a semiconductor substrate other than a silicon substrate may be used as the substrate. The bottom side of the N well NW may contact the P type epitaxial layer PEpi2. Here, the capacitor C6 is formed at the interface between the N well

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NW and the P type epitaxial layer PEpi2.

Fig. 2 is a cross-sectional view showing a semiconductor integrated circuit device 1b according to a second embodiment of the invention. As shown in Fig. 2, a P type silicon substrate Psub is provided in the semiconductor integrated circuit device 1b. The P type silicon substrate Psub has a resistivity of, for example, 10  $\Omega\cdot\text{cm}$ . The P type epitaxial layer PEpi2 is formed on the entire surface of the P type silicon substrate Psub. The P type epitaxial layer PEpi2 has a resistivity of, for example, 0.3  $\Omega\cdot\text{cm}$  and has a thickness of, for example, 1 to 5  $\mu\text{m}$ . The device forming portion 2 is provided on the P type epitaxial layer PEpi2. The structure of the device forming portion 2 is the same as that of the above-described first embodiment. That is, in the device forming portion 2, the P type epitaxial layer PEpi1 is provided and an N well NW and P well PW are alternately situated on the top surface of the P type epitaxial layer PEpi1. The bottom sides of the N well NW and P well PW are not in contact with the P type epitaxial layer PEpi2.

In the semiconductor integrated circuit device 1b, the P type epitaxial layer PEpi1 is connected to the ground terminal (not shown) via the P well PW, the p<sup>+</sup> diffusion region PD5, the via V11 and the wire W11. The N well NW is connected to the power supply terminal (not shown) via the n<sup>+</sup> diffusion region ND1, the via V1 and the wire W1. A pn

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junction is formed at the interface between the P type epitaxial layer PEpi1 and the N well NW, forming a capacitor C7 there.

According to this embodiment, the capacitor C7 can be  
5 formed between the P type epitaxial layer PEpi1 and the N well NW. This capacitor C7 serves as a decoupling capacitor connected in parallel to the power supply. The capacitor C7 shown in Fig. 2 equivalently shows a decoupling capacitor which is formed by the pn junction at the interface between  
10 the P type epitaxial layer PEpi1 and the N well NW. Because the decoupling capacitor can be formed locally in this embodiment (as compared to the first embodiment), an exclusive capacitor can be laid out near a region where power supply noise is likely to occur in a region which is  
15 susceptible to power supply noise. This can effectively suppress the adverse influence of power supply noise on the circuit. The other effects of the embodiment are the same as those of the first embodiment.

Although an example where the bottoms of the N well NW  
20 and the P well PW are not in contact with the P type epitaxial layer PEpi2 has been illustrated in the foregoing description of the second embodiment, the bottoms of the N well NW and the P well PW may contact the top surface of the P type epitaxial layer PEpi2. In this case, a capacitor is  
25 formed at the interface between the N well NW and the P type epitaxial layer PEpi2. The bottom side of the P type

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silicon substrate Psub may be connected to the power supply terminal.

Fig. 3 is a cross-sectional view showing a semiconductor integrated circuit device 1c according to a third embodiment of the invention. Figs. 4A and 4B are graphs showing the concentration distribution of the semiconductor integrated circuit device with the depth-directional position in the semiconductor integrated circuit device taken on the horizontal axis and the impurity concentration taken on the vertical axis. Fig. 4A shows the concentration distribution of the semiconductor integrated circuit device according to the third embodiment. Fig. 4B shows the concentration distribution of the semiconductor integrated circuit device according to the first embodiment.

As shown in Fig. 3, an N type silicon substrate Nsub is provided in the semiconductor integrated circuit device 1c. The N type silicon substrate Nsub has a resistivity of, for example,  $10\ \Omega\cdot\text{cm}$  and is connected to a power supply terminal (not shown) from its bottom side (not shown). The N type epitaxial layer NEpil is formed on the entire surface of the N type silicon substrate Nsub. The N type epitaxial layer PEpil has a resistivity of, for example,  $0.3\ \Omega\cdot\text{cm}$  and has a thickness of, for example, 1 to 5  $\mu\text{m}$ . The P type epitaxial layer PEpi2 is formed on the N type epitaxial layer NEpil. The P type epitaxial layer PEpi2 has a resistivity of, for example,  $0.3\ \Omega\cdot\text{cm}$ . The device forming portion 2 is then

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provided on the P type epitaxial layer PEpi2. The structure of the device forming portion 2 is the same as that of the first embodiment.

As shown in Fig. 4A, in the P type epitaxial layer  
5 PEpi1 of the semiconductor integrated circuit device 1c of the embodiment, the impurity concentration is, for example,  $1 \times 10^{15} \text{ cm}^{-3}$  from the top surface of the P type epitaxial layer PEpi1 to the interface between the P type epitaxial layer PEpi1 and the P type epitaxial layer PEpi2. In the P  
10 type epitaxial layer PEpi2, the impurity concentration is, for example,  $1 \times 10^{17} \text{ cm}^{-3}$ . Further, in the N type epitaxial layer NEpi1, the impurity concentration is, for example,  $1 \times 10^{17} \text{ cm}^{-3}$ . In the N type silicon substrate Nsub, the impurity concentration is, for example,  $1 \times 10^{15} \text{ cm}^{-3}$  and is  
15 constant in the depth direction. A pn junction with a high impurity concentration is realized at the interface between the P type epitaxial layer PEpi2 and the N type epitaxial layer NEpi1. Accordingly, a capacitor C2 (see Fig. 3) is formed at the interface between the P type epitaxial layer  
20 PEpi2 and the N type epitaxial layer NEpi1. The capacitor C2 functions as a decoupling capacitor connected in parallel to the power supply.

Because the N type epitaxial layer NEpi1 is not provided in the semiconductor integrated circuit device 1a  
25 according to the first embodiment, as shown in Fig. 4B, a pn junction is formed between the N type silicon substrate Nsub

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and the P type epitaxial layer PEpi2. Therefore, the impurity concentration at the interface of the pn junction in the first embodiment in Fig. 4B becomes lower than the impurity concentration at the interface of the pn junction  
5 in the third embodiment in Fig. 4A.

In this embodiment, a pn junction having a higher impurity concentration than that in the first embodiment can be realized by providing the N type epitaxial layer NEpi1 between the N type silicon substrate Nsub and the P type  
10 epitaxial layer PEpi2. This makes the capacitance of the capacitor C2 in the semiconductor integrated circuit device 1c of this embodiment greater than the capacitance of the capacitor C1 in the first embodiment. The other structure of the embodiment is the same as the corresponding structure  
15 of the first embodiment.

Fig. 5 is a cross-sectional view showing a semiconductor integrated circuit device 1d according to a fourth embodiment of the invention. As shown in Fig. 5, the N type silicon substrate Nsub having a resistivity of, for  
20 example,  $10\ \Omega\cdot\text{cm}$  is provided in the semiconductor integrated circuit device 1d. The bottom side of the N type silicon substrate Nsub, unlike that in the first and second embodiments, is not connected to the power supply terminal. A  $p^+$  diffusion region PD6 is selectively formed in the top  
25 surface of the N type silicon substrate Nsub. The  $p^+$  diffusion region PD6 has a resistivity of, for example,  $0.01$



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$\Omega$ -cm and has a thickness of, for example, 0.5 to 2  $\mu$ m.

The device forming portion 2 is provided on the N type silicon substrate Nsub. The structure of the device forming portion 2 is the same as the first embodiment. An n<sup>+</sup> diffusion region ND6 in the same layer as the P type epitaxial layer PEpil is formed in the region of the top surface of the N type silicon substrate Nsub where the p<sup>+</sup> diffusion region PD6 is not formed. This region is equivalent to an area lying directly below the N well NW of the device forming portion 2. This n<sup>+</sup> diffusion region ND6 becomes a contact region to secure conduction between the N type silicon substrate Nsub and the N well NW.

Accordingly, the power supply potential is applied to the N type silicon substrate Nsub N type silicon substrate Nsub from the power supply terminal (not shown) via the wire W1, the via V1, the n<sup>+</sup> diffusion region ND1, the N well NW and the n<sup>+</sup> diffusion region ND6. The ground potential is applied to the p<sup>+</sup> diffusion region PD6 from the ground terminal (not shown) via the wire W11, the via V11, the p<sup>+</sup> diffusion region PD5, the P well PW and the P type epitaxial layer PEpil. As a result, a capacitor C3 is formed at the interface between the N type silicon substrate Nsub and the p<sup>+</sup> diffusion region PD6.

In the embodiment, the capacitor C3 functions as a decoupling capacitor connected to the power supply. The area of the capacitor C3 can be controlled to adjust the

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capacitance of the capacitor C3 by controlling the area of the  $p^+$  diffusion region PD6. As the power supply potential is applied to the N type silicon substrate Nsub through the wire W1, it is unnecessary to connect the bottom side of the N type silicon substrate Nsub to the power supply terminal, thus making the mounting into a package easier. The other effects of embodiment are the same as those of the first embodiment.

Fig. 6 is a cross-sectional view showing a semiconductor integrated circuit device 1e according to a fifth embodiment of the invention. As shown in Fig. 6, the embodiment is a combination of the third embodiment and the fourth embodiment. Specifically, as shown in Fig. 6, the N type silicon substrate Nsub is provided in the semiconductor integrated circuit device 1e according to the embodiment. The bottom side of the N type silicon substrate Nsub is not connected to the power supply terminal. The N type epitaxial layer NEpil is formed on the N type silicon substrate Nsub. The N type epitaxial layer NEpil has a resistivity of, for example,  $0.3 \Omega\cdot\text{cm}$ . The  $p^+$  diffusion region PD6 is selectively formed on the top surface of the N type epitaxial layer NEpil. The  $p^+$  diffusion region PD6 has a resistivity of, for example,  $0.01 \Omega\cdot\text{cm}$ .

The device forming portion 2 is provided on the N type epitaxial layer NEpil. The structure of the device forming portion 2 is the same as the structure of the above-

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described first embodiment. Further, the  $n^+$  diffusion region ND6 is formed in the same layer as the P type epitaxial layer PEpil in the area of the top surface of the N type epitaxial layer NEpil where the  $p^+$  diffusion region PD6 is not formed, and which is equivalent to an area lying directly below the N well NW of the device forming portion 2. This  $n^+$  diffusion region ND6 becomes a contact region to secure conduction between the N type epitaxial layer NEpil and the N well NW.

10       The power supply potential is applied to the N type epitaxial layer NEpil via the wire W1, the via V1, the  $n^+$  diffusion region ND1, the N well NW and the  $n^+$  diffusion region ND6 shown in Fig. 1. The ground potential is applied to the  $p^+$  diffusion region PD6 via: the wire W11, the via V11, the  $p^+$  diffusion region PD5, the P well PW and the P type epitaxial layer PEpil. As a result, a capacitor C4 is formed at the interface between the N type epitaxial layer NEpil and the  $p^+$  diffusion region PD6.

20       In the embodiment, the capacitor C4 functions as a decoupling capacitor with respect to the power supply. As the impurity concentration of the N type epitaxial layer NEpil is higher than the impurity concentration of the N type silicon substrate Nsub, the capacitance of the capacitor C4 becomes larger than the capacitance of the capacitor C3 in the third embodiment. As the power supply potential is applied to the N type epitaxial layer NEpil

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through the wire W1, the bottom side of the N type silicon substrate Nsub need not be connected to the power supply terminal.

Further, as the current need not flow in the N type silicon substrate Nsub in the embodiment, the N type silicon substrate Nsub can be replaced with an arbitrary substrate. For example, using a high-resistance substrate having a resistivity of, for example, 100  $\Omega\cdot\text{cm}$  or higher, as the substrate can suppress the flow of noise current in the substrate. The other effects of the embodiment are the same as those of the first embodiment.

Fig. 7 is a cross-sectional view showing a semiconductor integrated circuit device 1f according to a sixth embodiment of the invention. As shown in Fig. 7, a high-resistance substrate Hsub is provided in the semiconductor integrated circuit device 1f according to the embodiment. The high-resistance substrate Hsub has a resistivity of, for example, 100  $\Omega\cdot\text{cm}$  or higher. The P type epitaxial layer PEpi2 is formed on the high-resistance substrate Hsub. The P type epitaxial layer PEpi2 has a resistivity of, for example, 0.3  $\Omega\cdot\text{cm}$ . A device forming portion 12 is provided on the P type epitaxial layer PEpi2.

In the device forming portion 12, a P type epitaxial layer PEpi3 is provided selectively on the P type epitaxial layer PEpi2. The P type epitaxial layer PEpi3 has a resistivity of, for example, 10  $\Omega\cdot\text{cm}$  and has a thickness of,

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for example, 1 to 5  $\mu\text{m}$ . A  $\text{p}^+$  diffusion region PD7 is provided selectively in that region where the P type epitaxial layer PEpi3 is not provided, and an  $\text{n}^+$  diffusion region ND7 is provided on the  $\text{p}^+$  diffusion region PD7. The  $\text{p}^+$  diffusion region PD7 has a resistivity of, for example, 1  $\Omega\cdot\text{cm}$  and the  $\text{n}^+$  diffusion region ND7 has a resistivity of, for example, 1  $\Omega\cdot\text{cm}$ . The total thickness of the  $\text{p}^+$  diffusion region PD7 and the  $\text{n}^+$  diffusion region ND7 is equal to the thickness of the P type epitaxial layer PEpi3. The double-layer film comprised of the  $\text{p}^+$  diffusion region PD7 and the  $\text{n}^+$  diffusion region ND7 is formed in the same layer as the P type epitaxial layer PEpi3. The P well PW is provided on the P type epitaxial layer PEpi3, and the N well NW is provided on the  $\text{n}^+$  diffusion region ND7. The other structure of the device forming portion 12 is the same as the corresponding structure of the device forming portion 2 (see Fig. 1) in the first embodiment.

In the semiconductor integrated circuit device 1f, the power supply potential is applied to the  $\text{n}^+$  diffusion region ND7 via the: wire W1, via V1,  $\text{n}^+$  diffusion region ND1, and N well NW. The ground potential is applied to the  $\text{p}^+$  diffusion region PD7 via the: wire W11, via V11,  $\text{p}^+$  diffusion region PD5, P well PW, P type epitaxial layer PEpi3 and P type epitaxial layer PEpi2. This forms a capacitor C5 at the interface between the  $\text{p}^+$  diffusion region PD7 and the  $\text{n}^+$  diffusion region ND7.

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In the embodiment, the capacitor C5 functions as a decoupling capacitor connected in parallel to the power supply. Using the high-resistance substrate having a resistivity of  $100\ \Omega\cdot\text{cm}$  or higher as the substrate can suppress the flow of noise current in the substrate. In the embodiment, the decoupling capacitor can selectively be formed directly below the N well NW. Therefore, an exclusive capacitor can be laid out near a circuit region where power supply noise is likely to occur and a circuit region which is susceptible to power supply noise. This can effectively suppress the adverse influence of power supply noise on the circuit, and thereby improve the implementability of the noise suppressing effect. The other effects of the embodiment are the same as those of the first embodiment.

Although an example where the capacitor C5 is formed directly under the N well NW has been illustrated in the foregoing description of the sixth embodiment, the invention is not limited to this particular structure, as the capacitor may be formed directly under the P well PW. In this case, an N type layer, e.g., an N type epitaxial layer, should be provided on the high-resistance substrate  $H_{\text{sub}}$ , and an  $n^+$  diffusion region and a  $p^+$  diffusion region should be formed in order on the N type layer in such a way that the  $p^+$  diffusion region would be connected to the P well.